NSN 5961-01-351-4855

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-351-4855 **Inclosure Material:** Metal **Overall Length:** 0.38 millimeters **Overall Height:** 0.13 millimeters **Overall Width:** 0.38 millimeters **Function For Which Designed:** Frequency multiplier **Mounting Method:** Press fit **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 20.0 breakdown voltage, dc **Current Rating Per Characteristic:** 10.00 microamperes operating voltage dc absolute **Power Rating Per Characteristic:** 100.0 milliwatts small-signal input power, common-collector preset **Capacitance Rating In Picofarads:** 0.4 **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius ambient air **Precious Material And Location:** Terminals gold **Precious Material:** Gold **Terminal Type And Quantity:** 1 bonding pad Shelf Life: N/a **Unit Of Measure: Demilitarization:**

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